

Alphabet Soup

An Overview of Diagnostic Techniques

John Smedley and Matt Poelker

What we want to know

Crystalline cathodes (Diamond, GaAs, metals)

Surface orientation, texture, grain size, defect density and type, strain, multilayer spacing and properties

Surface chemistry, contamination, termination

Bulk impurities, doping levels

Surface morphology, spatial variation

Electronic and emission characteristics: energy/momentum spread, QE, temporal response, carrier velocity, trapping, carrier lifetime/escape depth, scattering, density of states

Grown Cathodes (Cs_2Te , Cs_3Sb , CsK_2Sb)

As above, plus film thickness and uniformity

In situ diagnostics during growth

Diffraction

X ray diffraction (XRD) provides information on crystal structure, grain size and texture, strain

Grazing Incidence (GID) improves surface sensitivity

Topography provides strain and defect image

(Jean's talk)

Electron diffraction (LEED, RHEED) provides surface orientation, including reconstruction

Electron Backscattered Diffraction (EBSD) provides spatially resolved grain maps

Photoemission Spectroscopy

Ultraviolet Photoemission Spectroscopy (UPS)

Angle Resolved (ARPES) – valence band structure, momentum band structure, emission characteristics, electron/phonon coupling, scattering

Photoemission electron microscope (PEEM) -
Spatially resolved electron emission

X-ray Photoemission Spectroscopy (XPS)

Surface chemical composition, contamination

Absorption/Fluorescent Spectroscopy

X-ray Fluorescence (XRF) provides elemental analysis

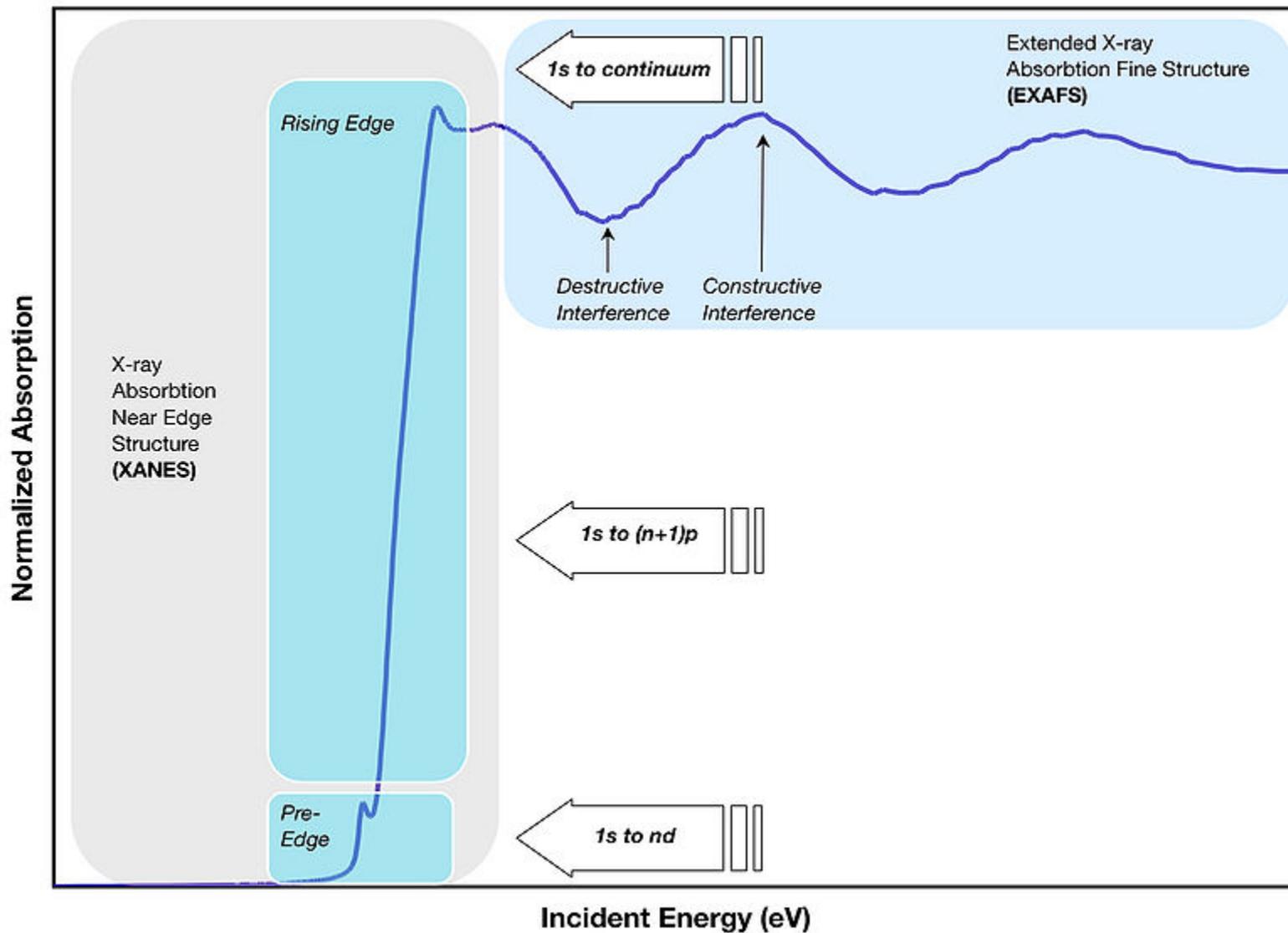
Can be stimulated with X-ray or Electron beams

Energy Dispersive X-ray Spectroscopy (EDS) provides spatial resolved elemental composition

X-ray Absorption Spectroscopy (XAS)

Measure electron yield or fluorescent yield for near edge analysis (NEXAFS/XANES) – provides surface or bulk chemical information, joint density of states

Measure absorption or fluorescence for “extended” structure (>100 eV above edge, EXAFS) – provides information on local atomic environment due to photoelectron scattering



Other Spectroscopy

Infrared Spectroscopy (FTIR) – Vibrational modes, Impurity content, doping level, typically spatially resolved

Raman Spectroscopy – phonon/vibration modes, material identification

Photoluminescence (PL) – Impurities, intra band states in semiconductors, electronic impact of crystalline defects

Total Yield Spectroscopy (TYS) – QE vs photon energy, indirect information on density of states and scattering mechanisms

Imaging

Scanning Electron Microscopy (SEM)

Surface scanning

Atomic Force Microscopy (AFM) and Profilometry

Kelvin Probe Force Microscopy (KPFM)

Local work function

Scanning Tunneling Microscope (STM)

Local density of states

Combined w/ other techniques (PEEM, XBIC,
Topography)

Induced Current

Beam induced current (BIC) provides carrier dynamics (mobility, saturation velocity, lifetime, trapping sites, contact type) with spatial resolution determined by beam size and rastering capability

Electron, X-ray and Ion beams are used (EBIC, XBIC, IBIC)

XBIC provides the ability to probe depth

EBIC provides SEM spatial resolution

IBIC provides “delta function” temporal response

Diamond Science at BNL

Imaging

SEM Scanning Electron Microscopy Surface morphology

LEEM Low Energy Electron Microscopy Imaging of hydrogenated surface, spatially localized LEED, work function mapping

AFM Atomic Force Microscopy Surface morphology

Diffraction

XRD X-ray diffraction, time resolved Characterization of metal contacts, including temperature of formation and crystalline texture

XRD X-ray diffraction Diamond crystal quality; evaluation of stress caused by laser shaping

Topography Diamond crystal quality, localization and identification of defects

LEED Low Energy Electron Diffraction Surface crystal analysis, evaluation of hydrogenated surface

Spectroscopy

UPS/ARPES Ultraviolet Photoemission Spectroscopy Electron affinity, energy & angular distribution of emitted electrons, lifetime of NEA surface

TYS Total Yield Spectroscopy Evaluation of hydrogenated surface, lifetime

NEXAFS Near Edge X-ray Absorption Fine Structure Surface elemental analysis, characterization of surface bonding, carbon formation

XAFS X-ray absorption fine structure Titanium/diamond surface chemistry

EDS Energy Dispersive X-ray Spectroscopy Surface elemental analysis

FTIR Fourier Transform Infrared Spectroscopy Impurities in diamond

Photoluminescence & Raman Spectroscopy Impurity analysis, identification of carbon chemistry, mapping

Carrier Transport and Emission

Electron Generated Carrier Transport vs Field, Emission, Gain, Thermal Emittance

Photo-electron Generated Gain, Timing

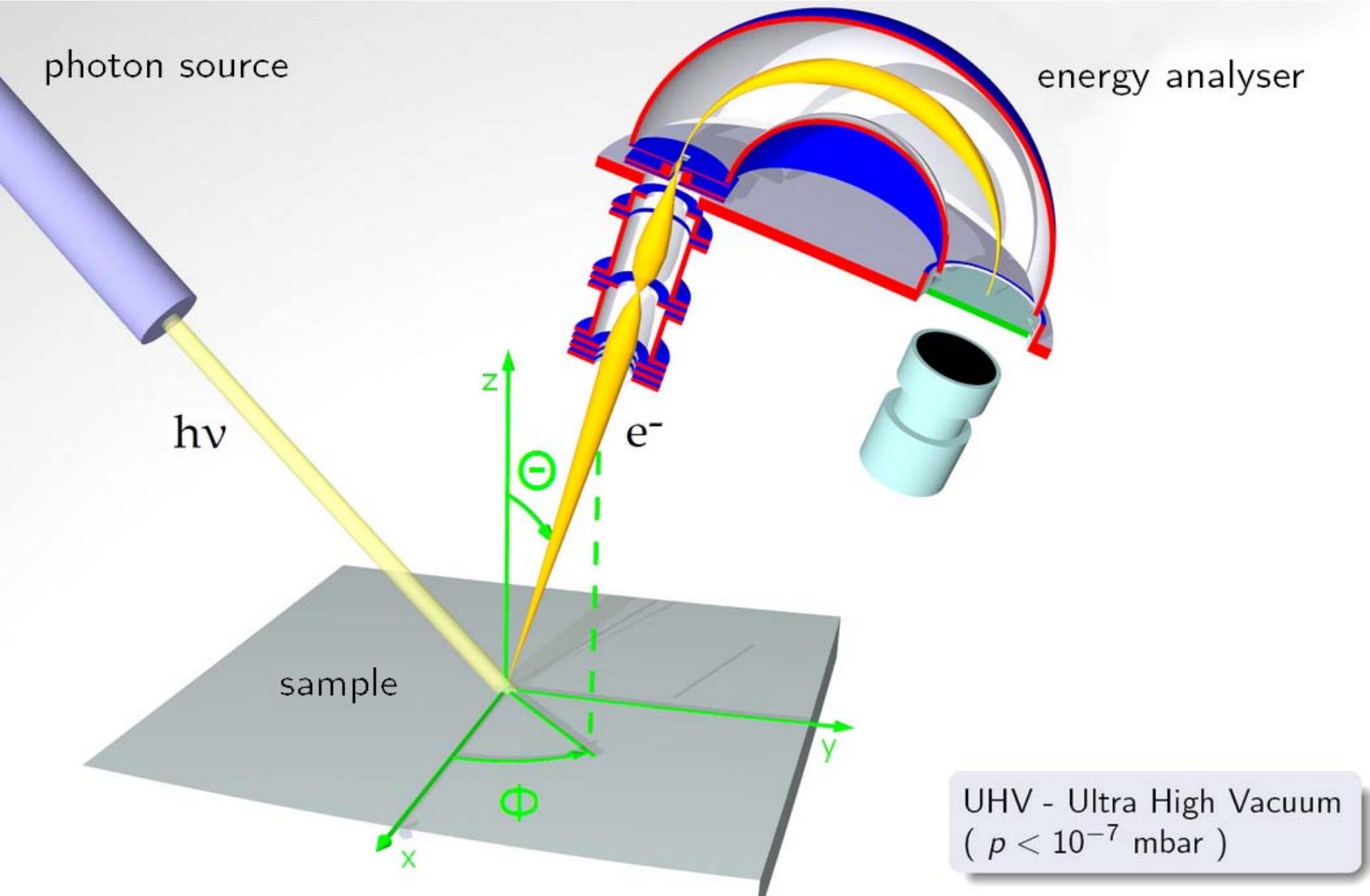
Soft X-ray, Monochromatic Charge collection distance, Charge trapping/detrapping effects

Hard X-ray, Monochromatic Measurement of mean ionization energy (gain)

High Flux White beam Current Limits, Contact requirements, Heat management

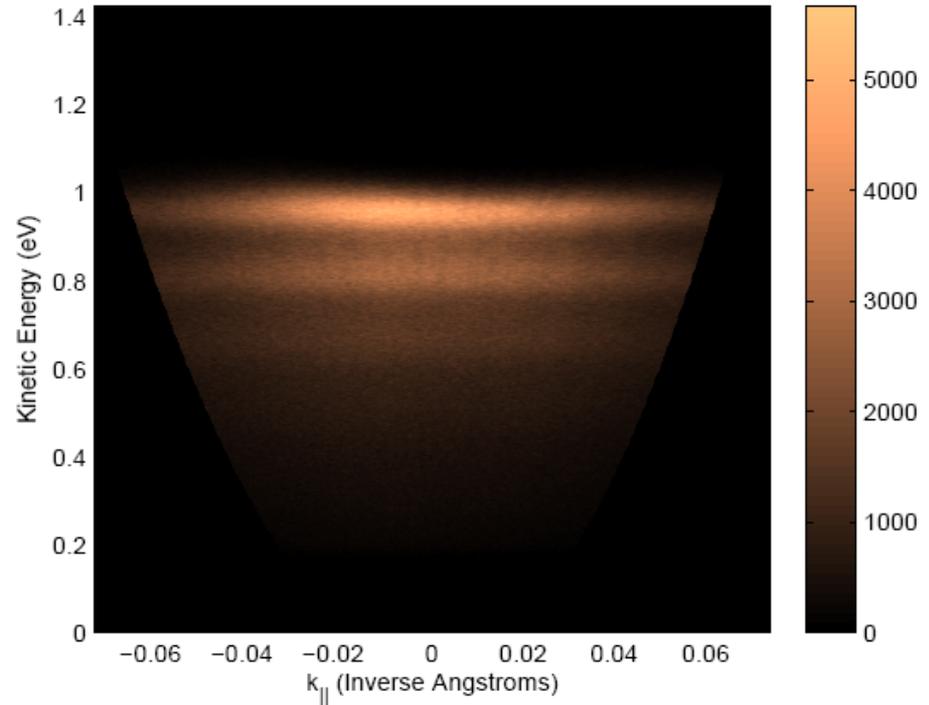
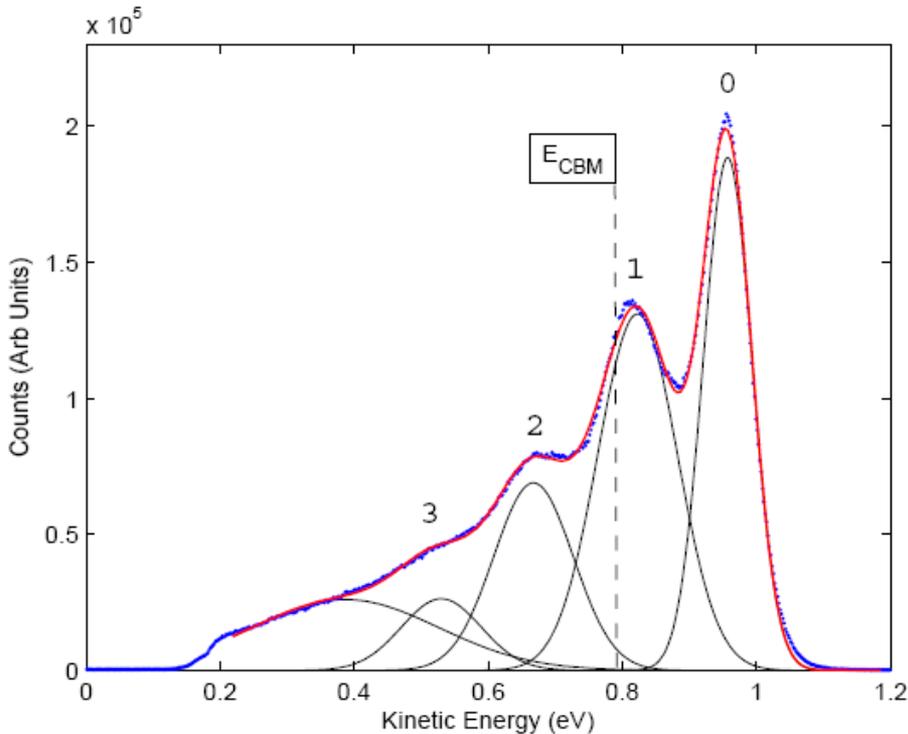
Micro-beam Mapping Localization of electrically active sites

Angle-Resolved Photoemission Spectroscopy



Laser ARPES

Boron Doped Diamond, H Terminated, [001]



Used 6 eV photons – below direct transition band gap

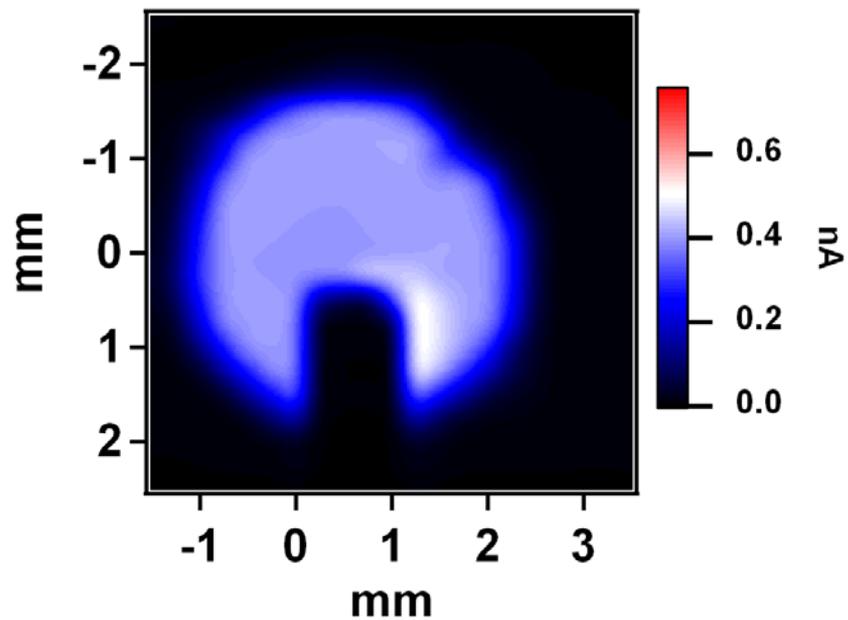
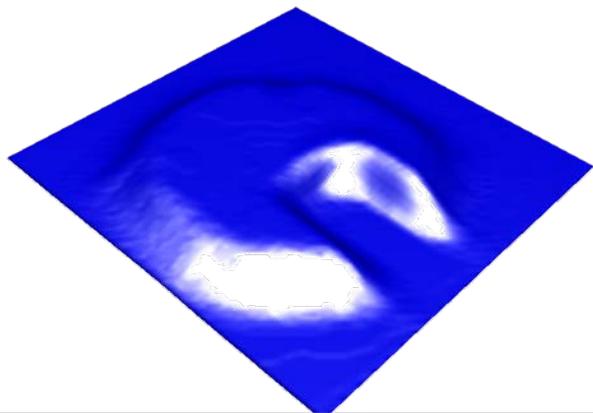
(synchrotron ARPES gives direct PE behavior- no thermalization)

Max KE = NEA \sim 1 eV, as expected from theory

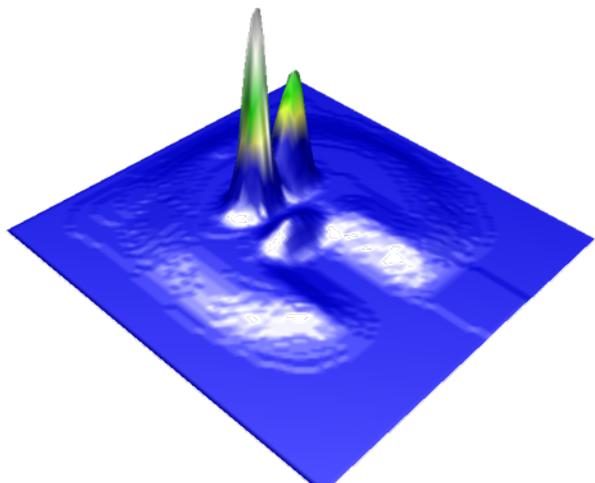
Spectrum is isotropic over at least 30 degrees from normal

Discrete peaks caused by phonon scattering – may depend on doping level

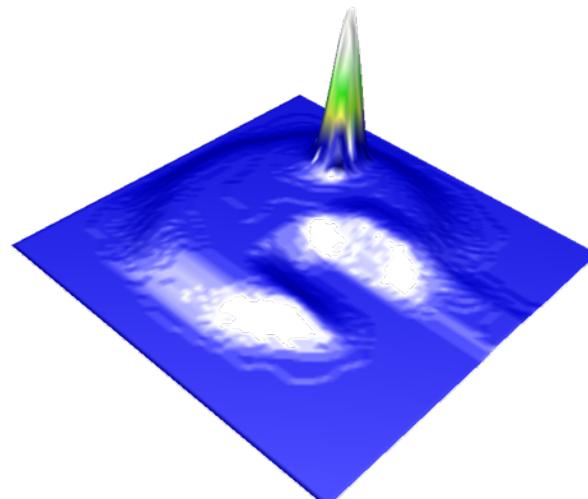
HID14 in X15
(80%, 100V, 1kHz, 19keV)



HID18 in X6B
(80% , -100V, 1kHz, 19keV)

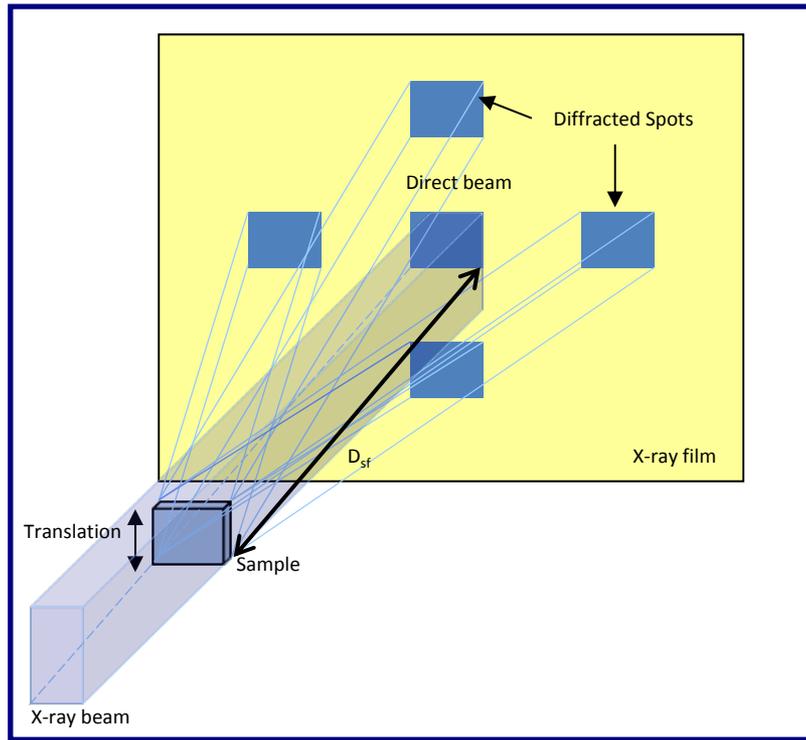


HID18 in X6B
(80% , +100V, 1kHz, 19keV)

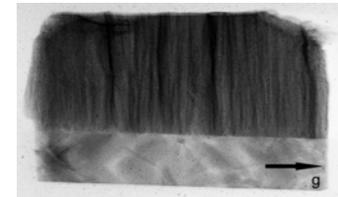
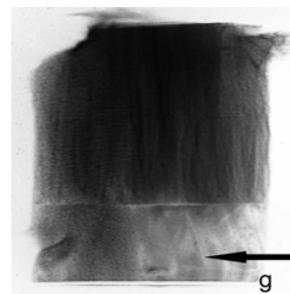
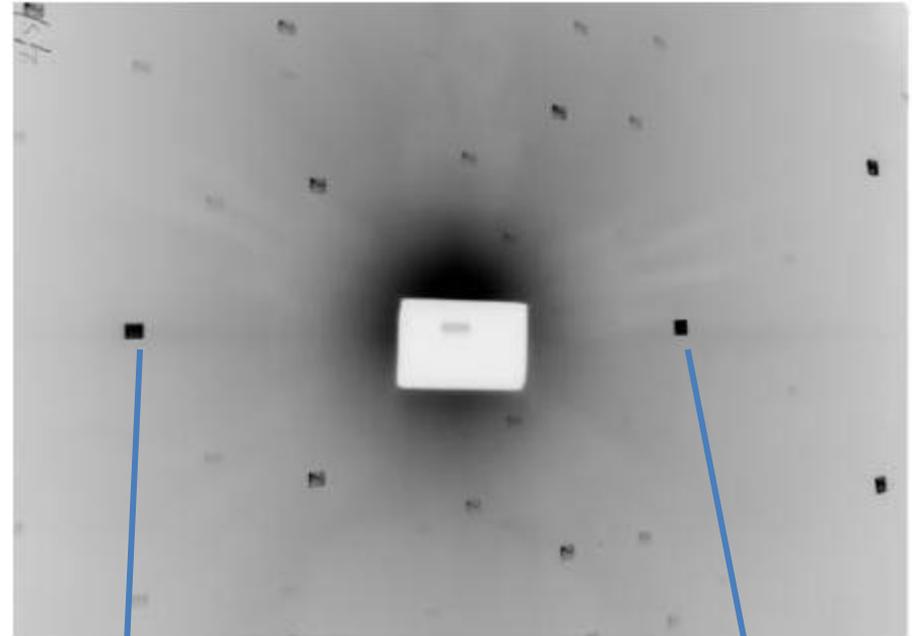


X-ray Topography

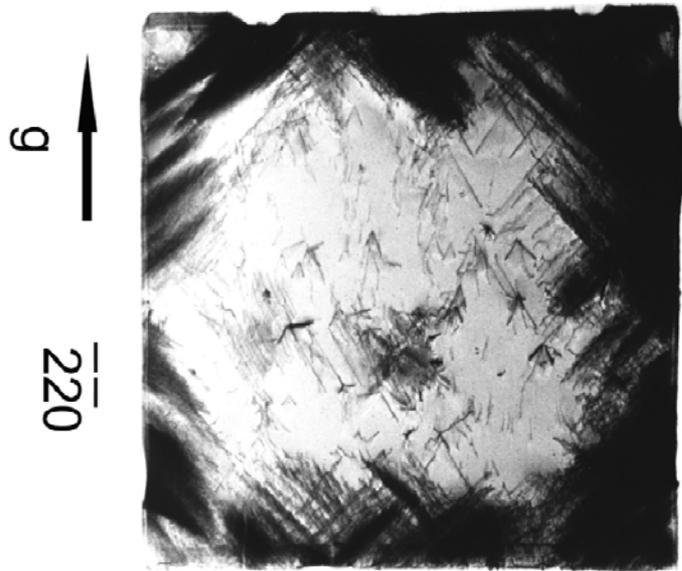
Transmission



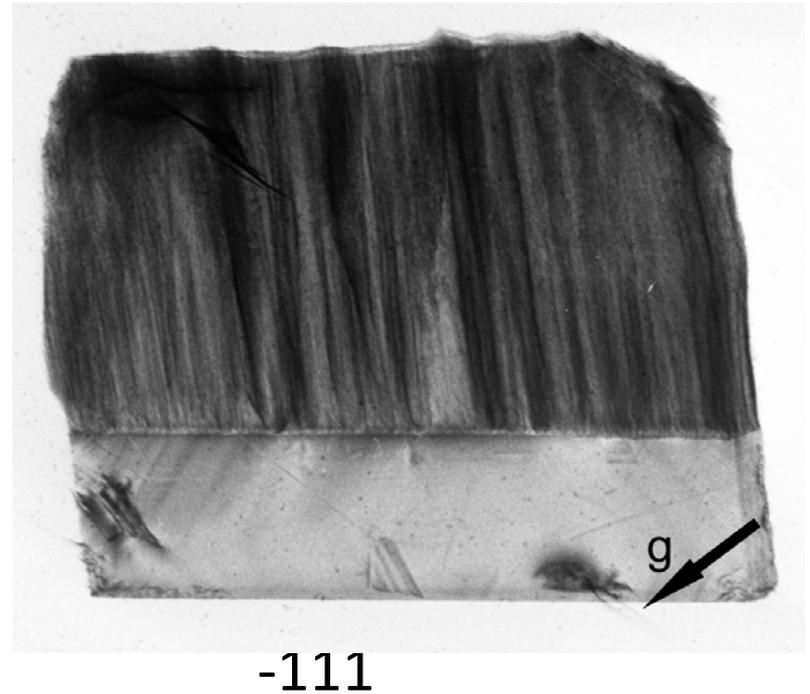
The diamond is placed on a stage that can be rotated to record various reflections like the $\{220\}$ s, $\{400\}$ s and $\{111\}$ s below.



White Beam Topography



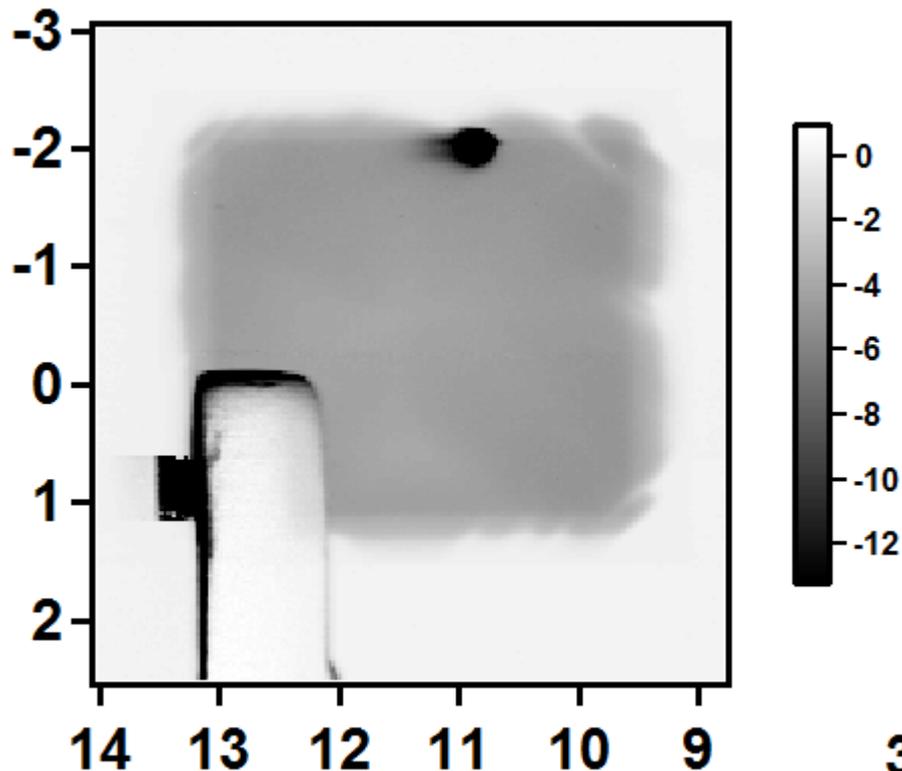
Single crystal CVD – slip bands near edges, threading dislocations throughout



Vertically cut sample shows HPHT substrate which has significantly superior crystal quality but very poor charge transport. Most threading dislocations source at substrate.

Thanks to B. Raghothamachar, M. Dudley (X19C), A. Lohstroh for vertical cut sample

X-ray Response Mapping, Revisited



HID15 w/ annealed Pt contacts

Single photoconductive region

Slip bands reduce responsivity

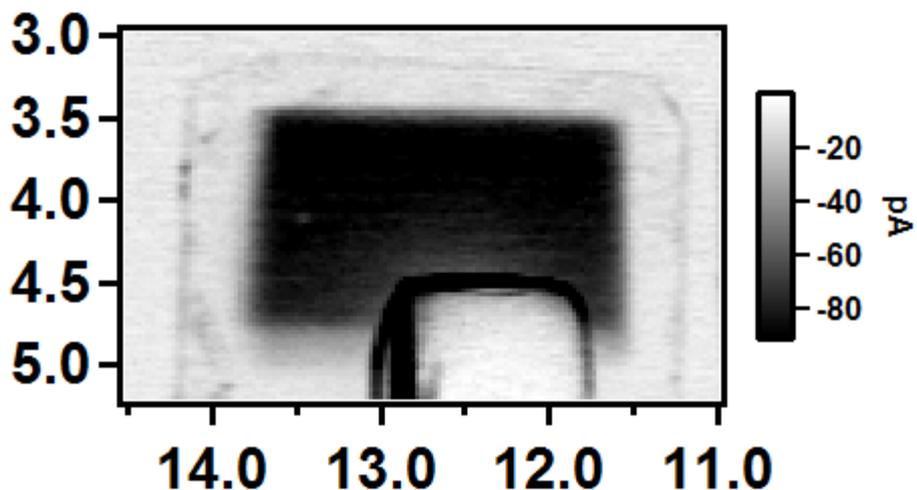
near edges for both polarities

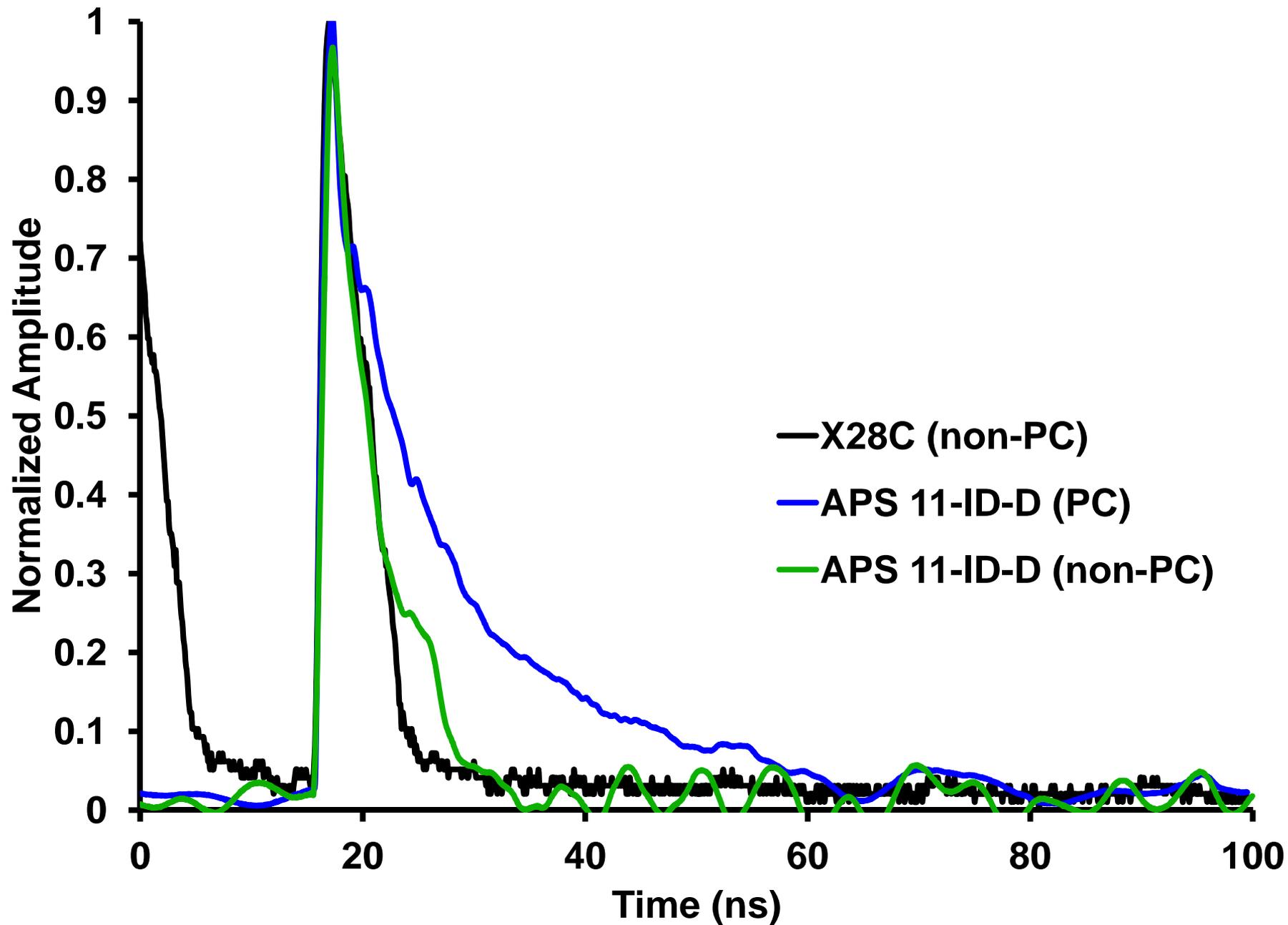
Center has expected “diode”
response

Vertical diamond

Sub “diode” response

Substrate has very low
response





Temporal response, Soft X-rays

8.674E-18

Voltage (V)

-0.005

-0.01

-0.015

0

5

10

15

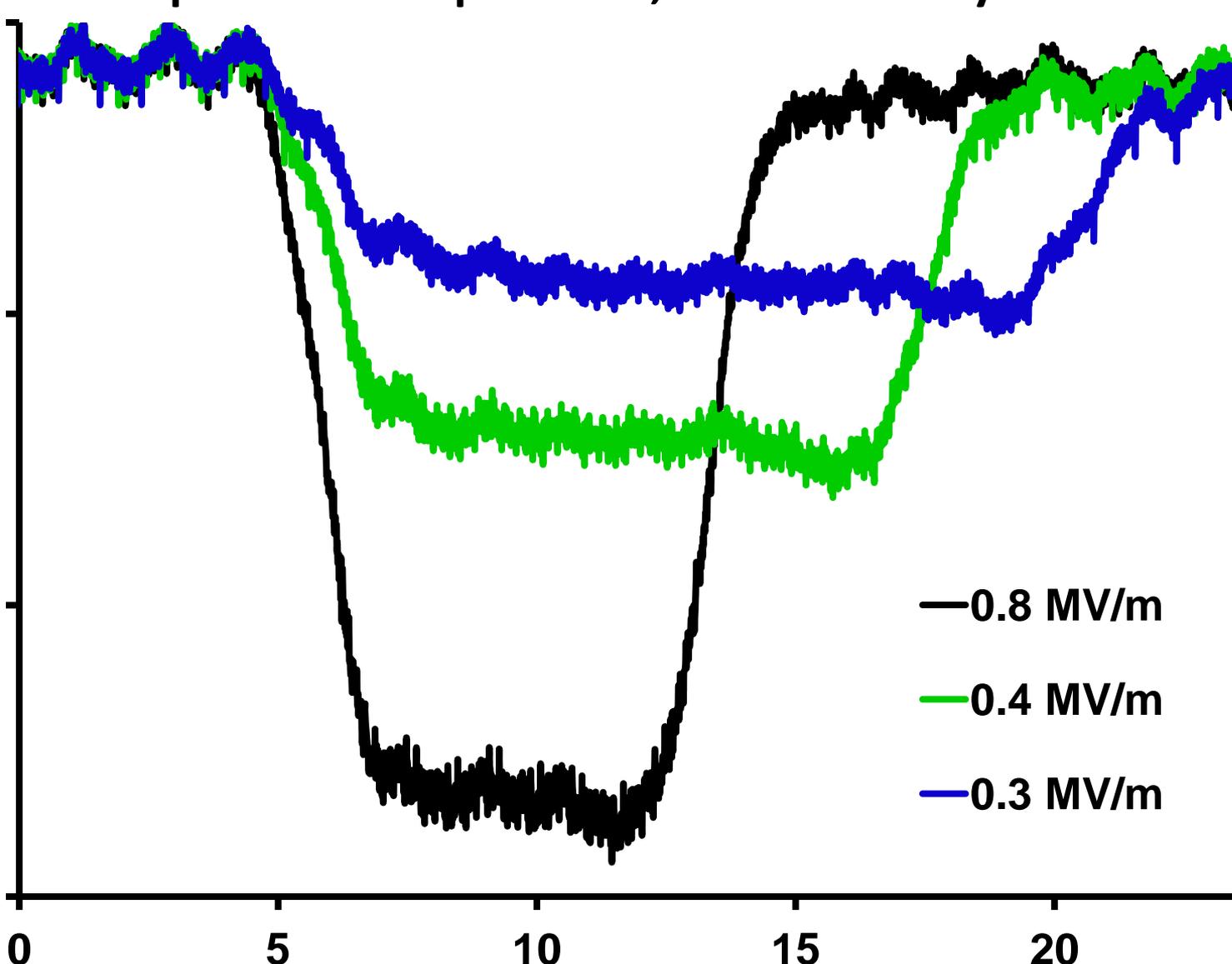
20

Time (ns)

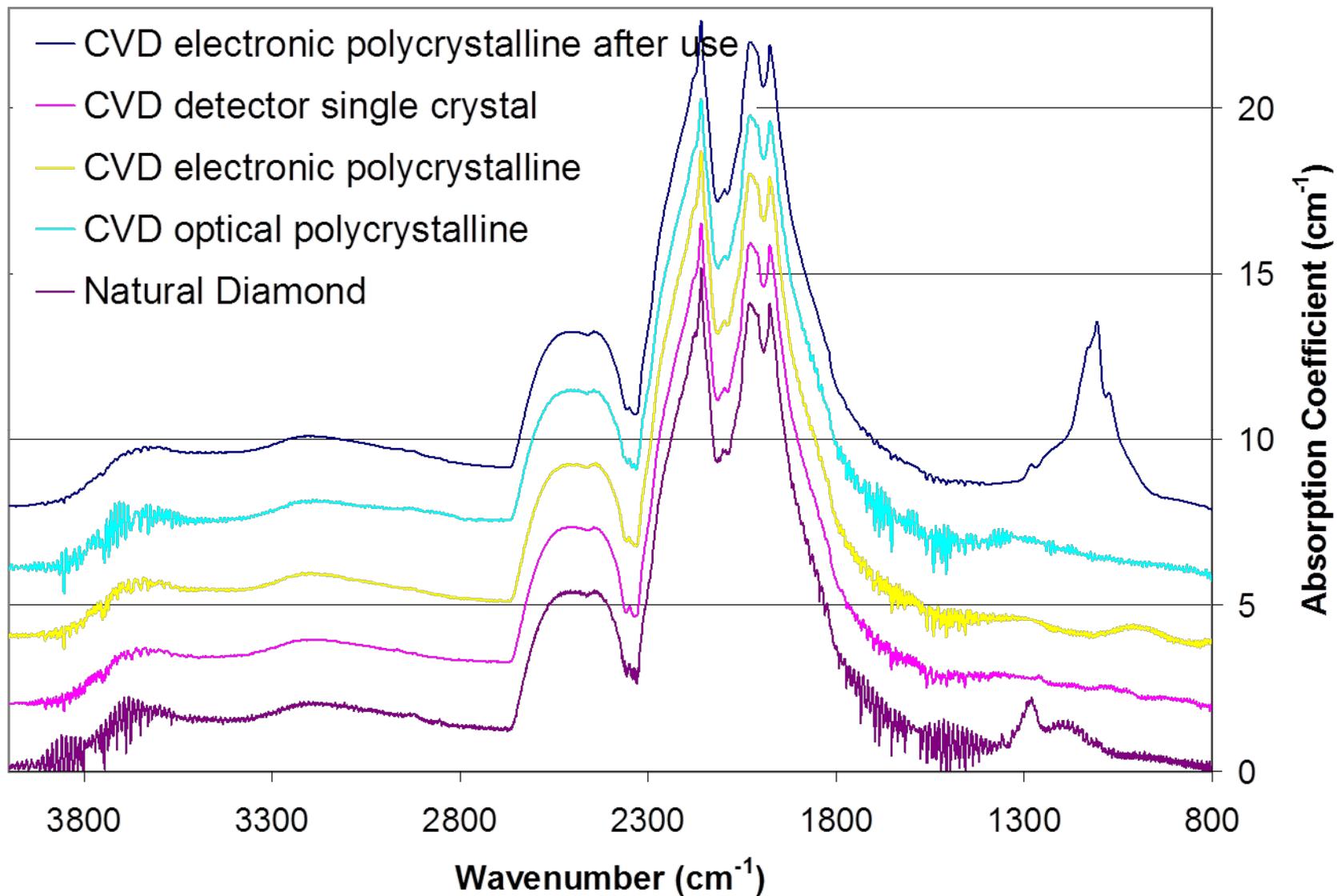
— 0.8 MV/m

— 0.4 MV/m

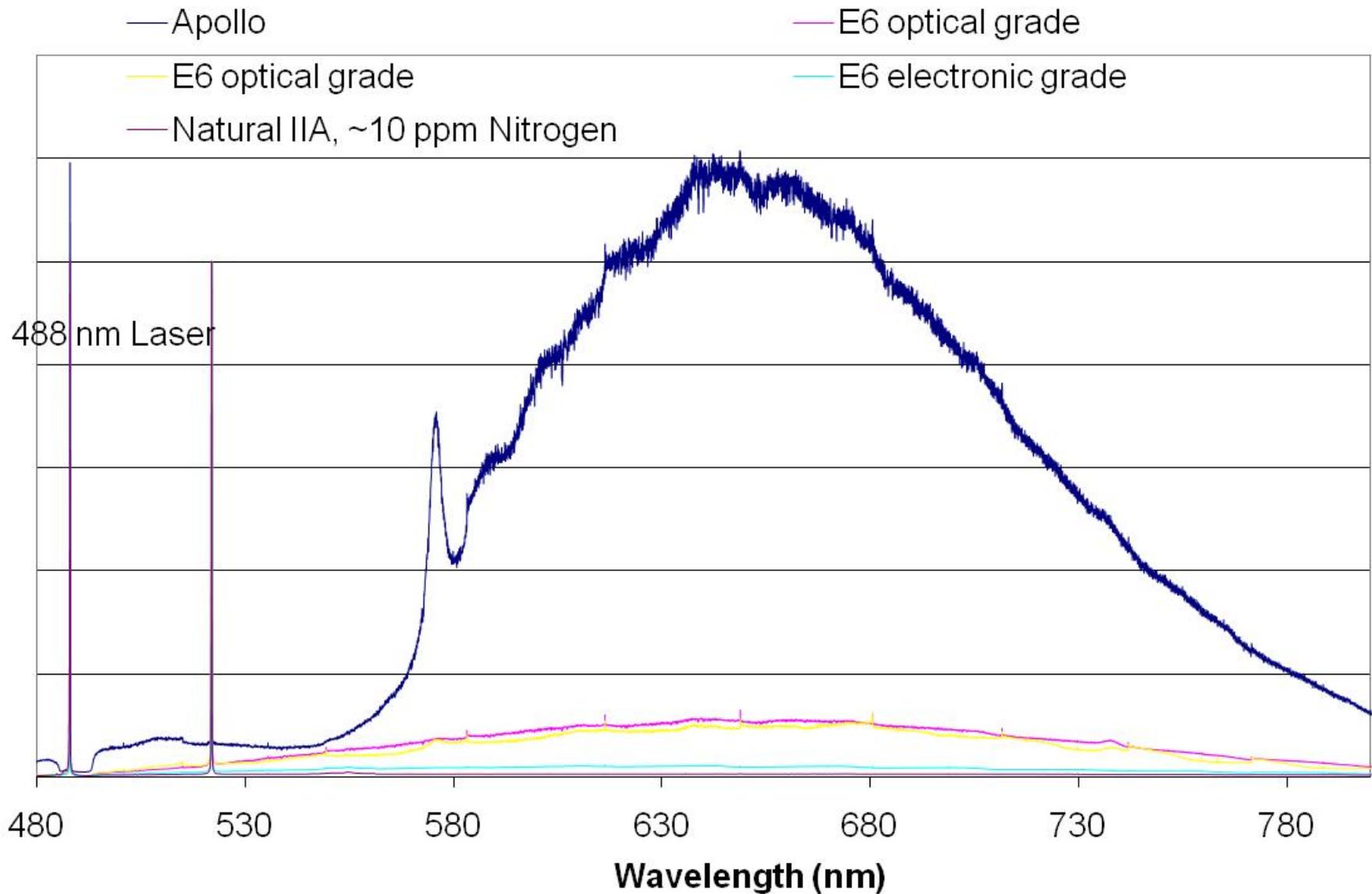
— 0.3 MV/m

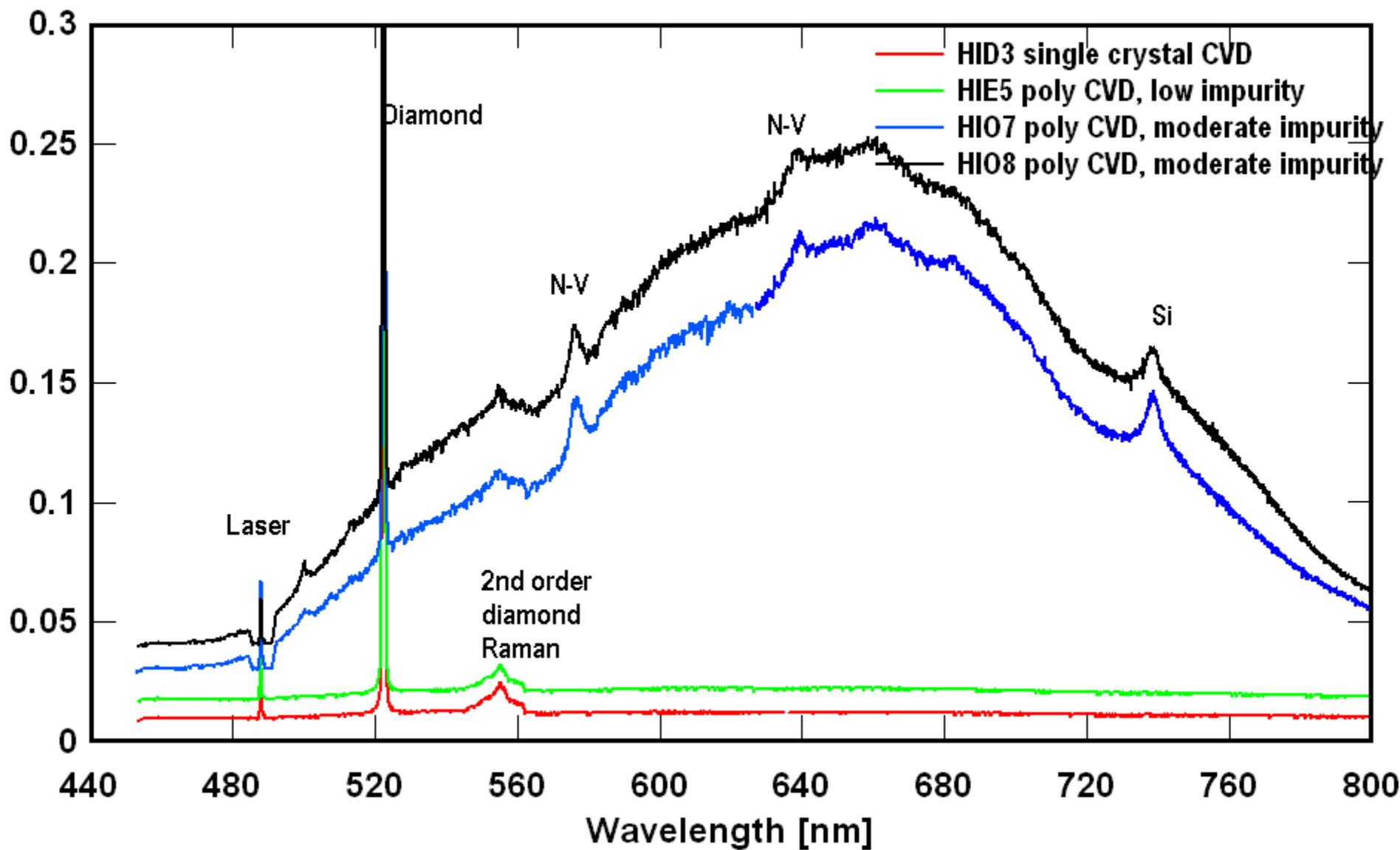


IR Spectroscopy (FTIR)



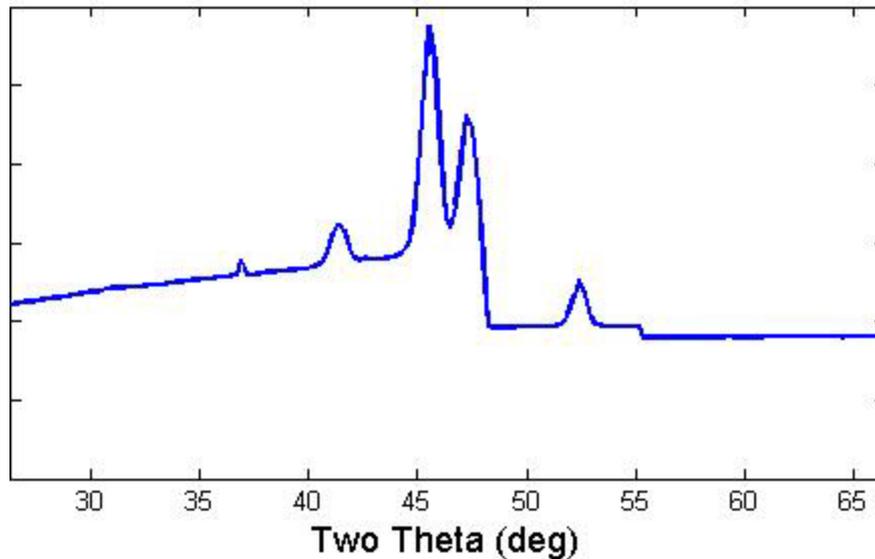
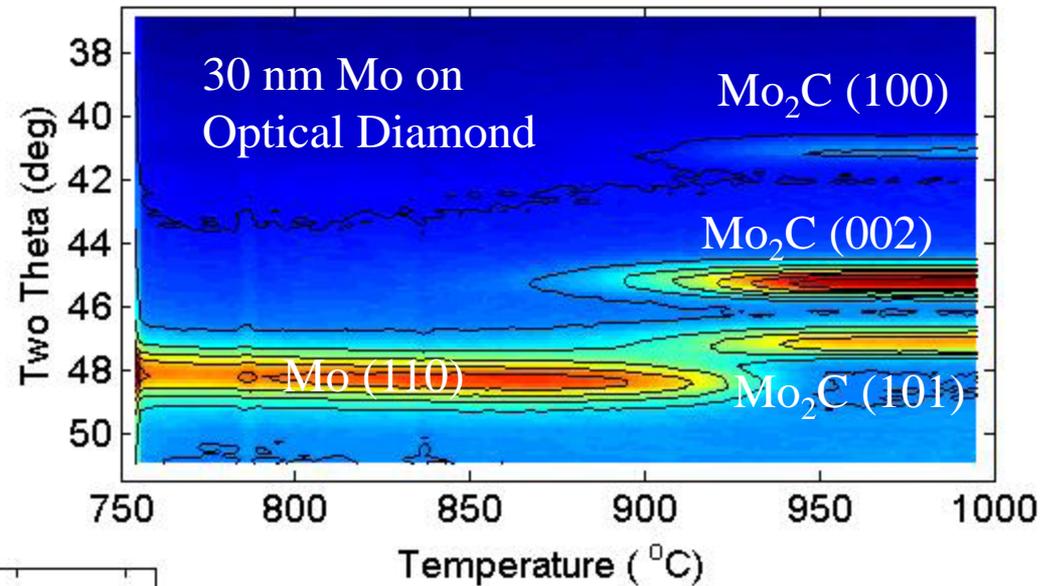
Photoluminescence





Metallization & Carbide Formation

Investigate carbide forming metals (Ti, Nb Mo) via in-situ XRD



Molybdenum is attractive
- avoid capping Pt layer

J. Appl. Phys. **99** 063740

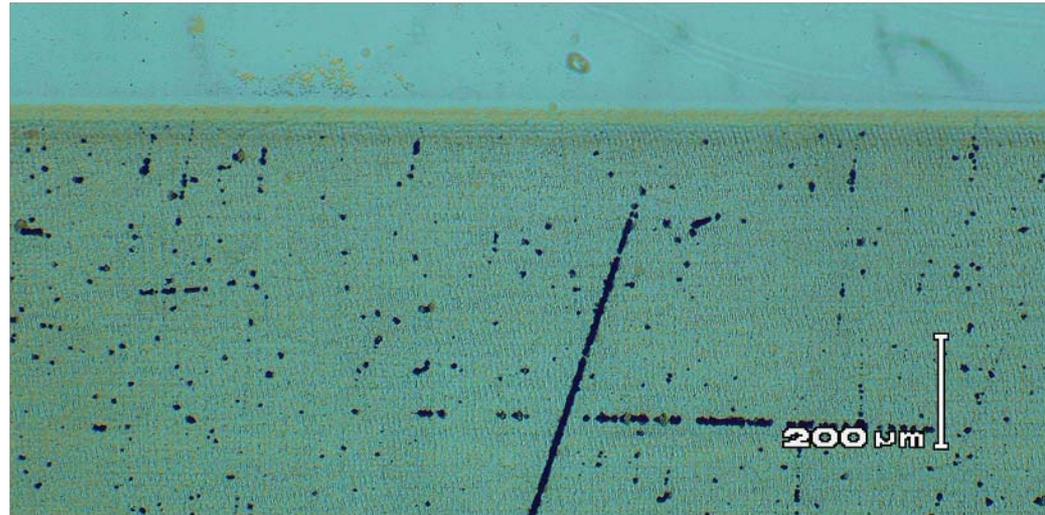
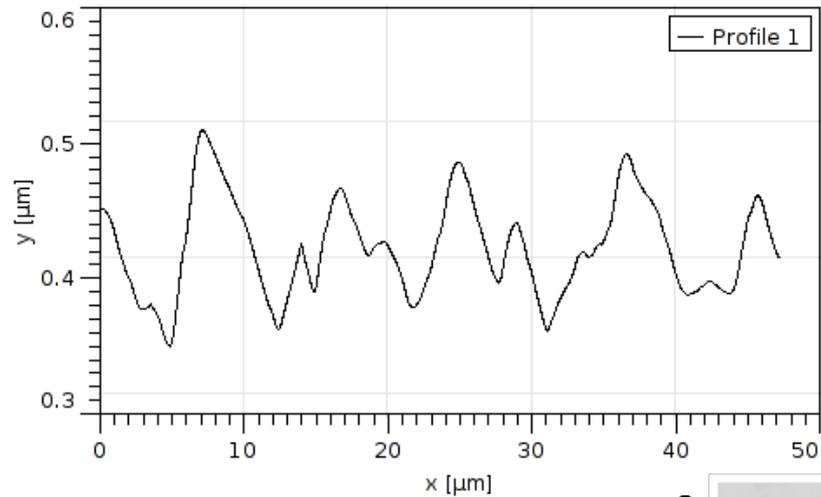
J. Appl. Phys. **101** 053714

Diamond Thinning and Shaping

Laser Ablation

Fast* (up to $0.3\mu\text{m/s}$)

Easy to Pattern



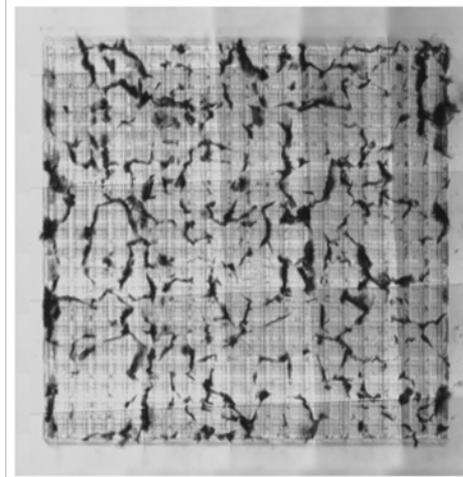
266nm, FWHM = $27\mu\text{m}$, 30ps, $100\mu\text{J}$, 10Hz
10μm interleaved raster, SC diamond, $2\mu\text{m}$ depth

But

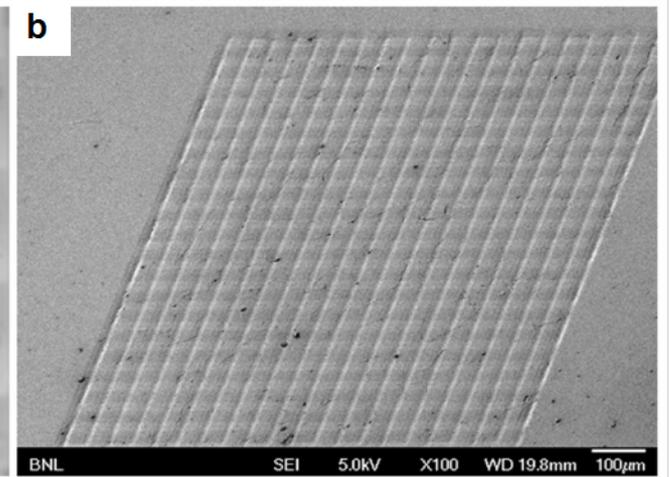
Induces strain

Non-diamond C

a



b

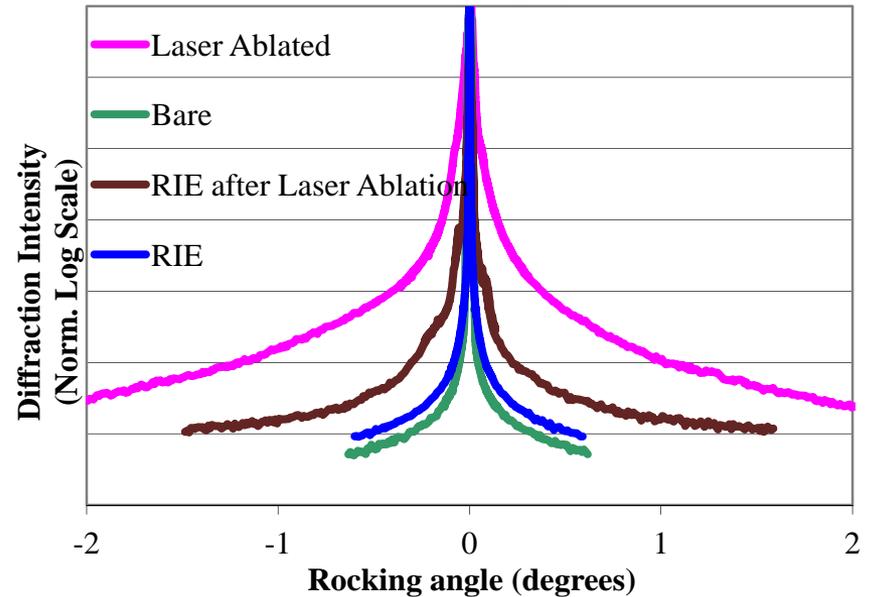
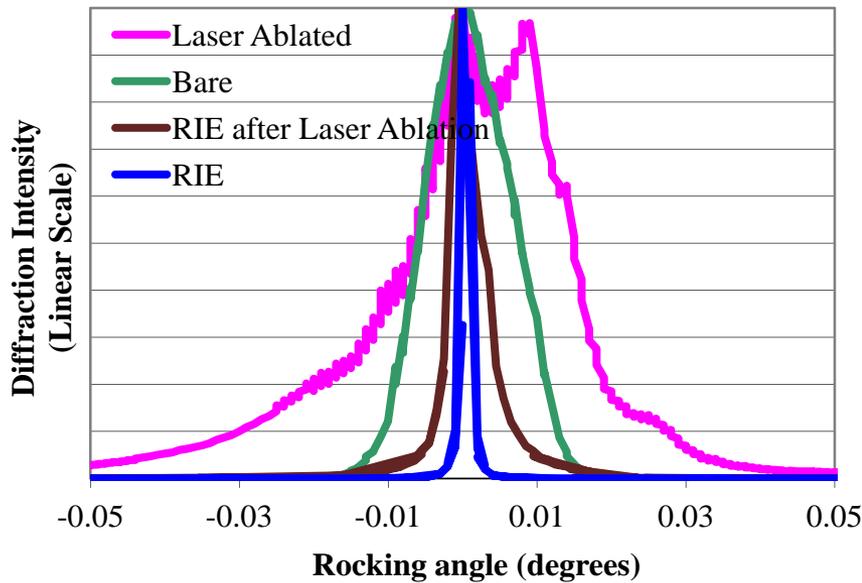
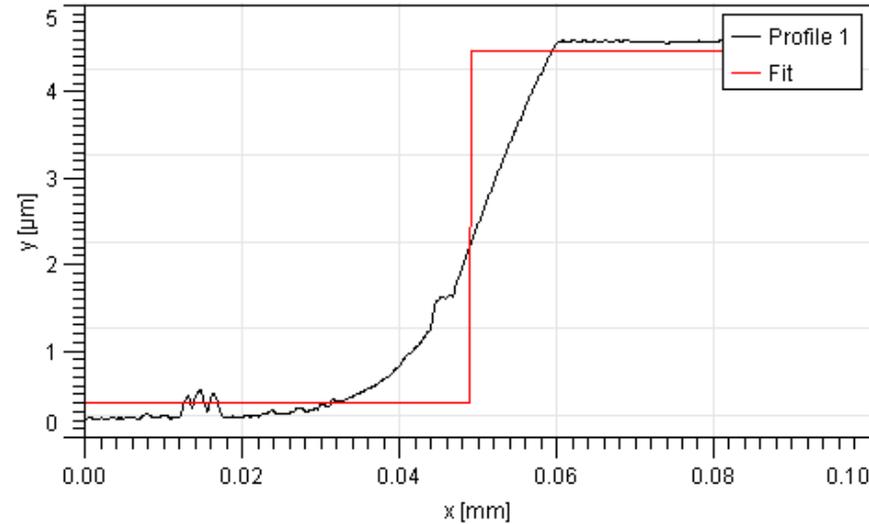
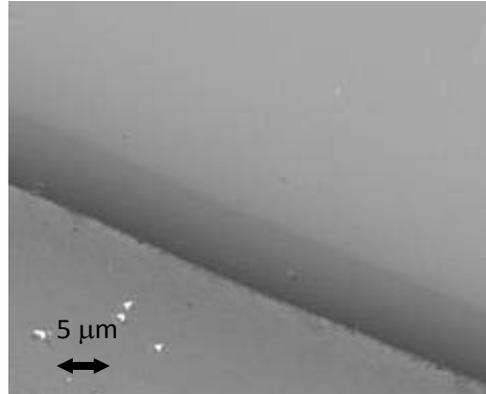


*George T., et al, Appl. Phys Lett. **62**, 2880 (1993)

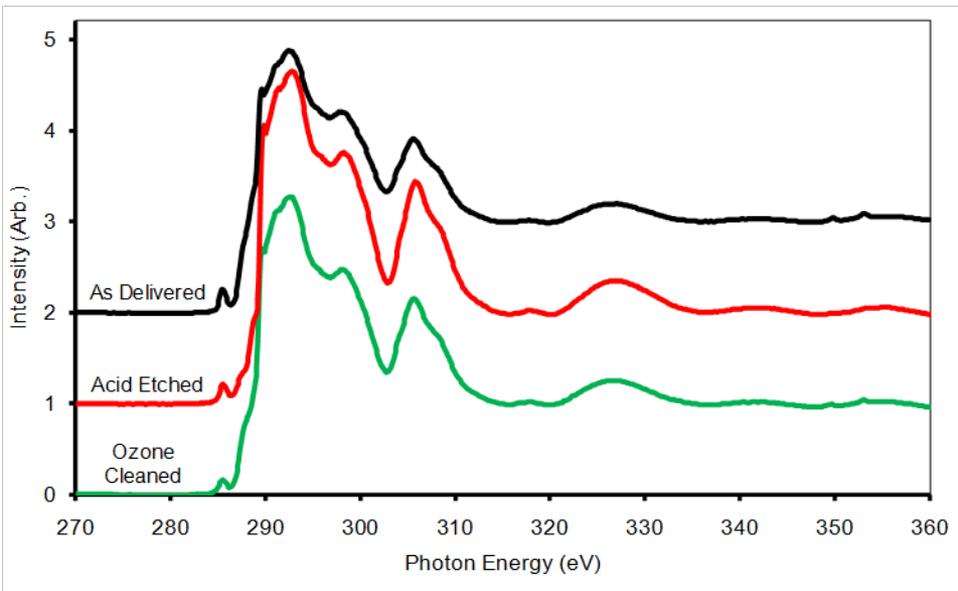
Reactive Ion Etching

ICP RIE

50 sccm O₂/ 8sccm Ar
850W P_{ICP}, 15W of P_{RF}
65–80nm/min.
Removes Strain Layer

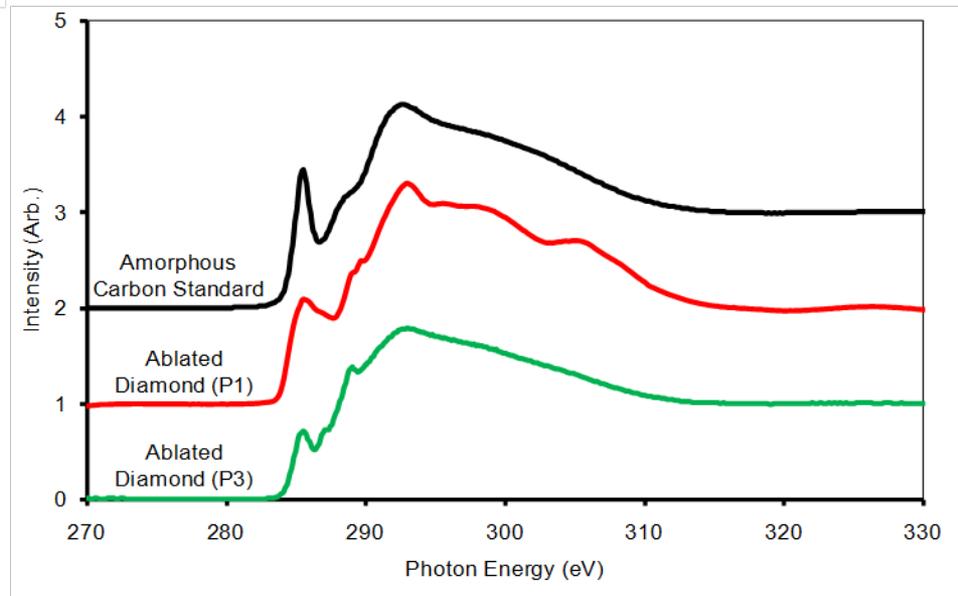


Non Diamond Carbon



Carbon edge NEXAFS shows small NDC contaminant on the surface of the diamonds, easily removed with acid etching or ozone cleaning

After laser ablation, the surface is entirely amorphous carbon



Ozone Cleaning

6 hrs of exposure to UV lamp in air reduced non-diamond carbon thickness by at least x4

**IR Transmission
Referenced to Unablated Diamond**

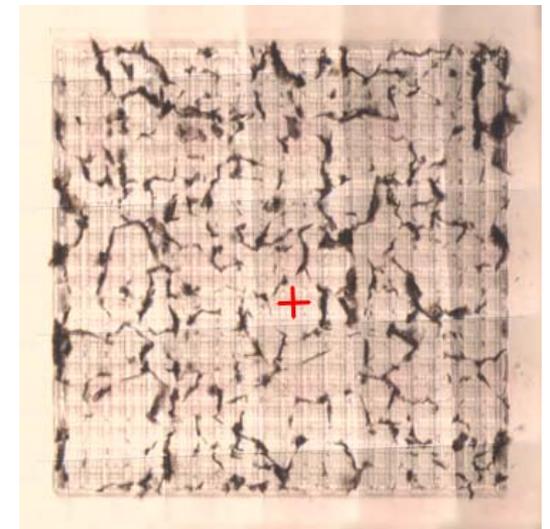
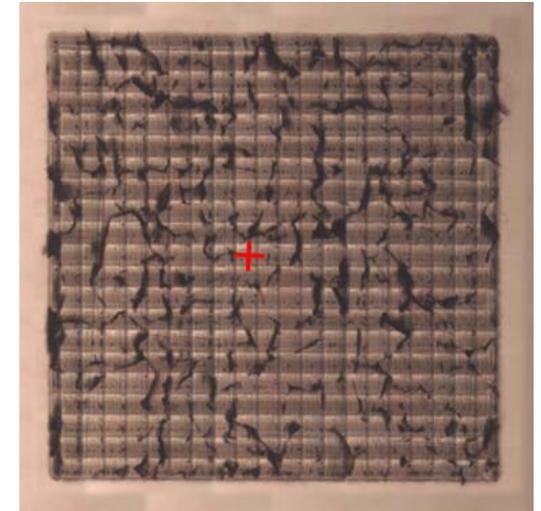
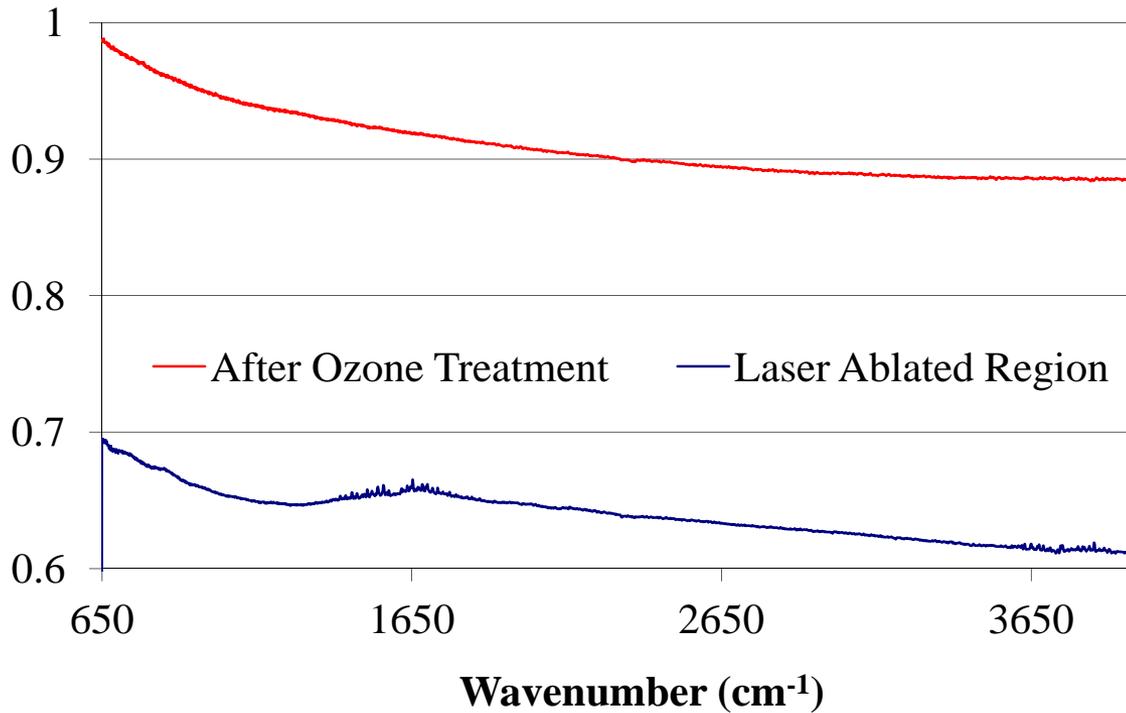
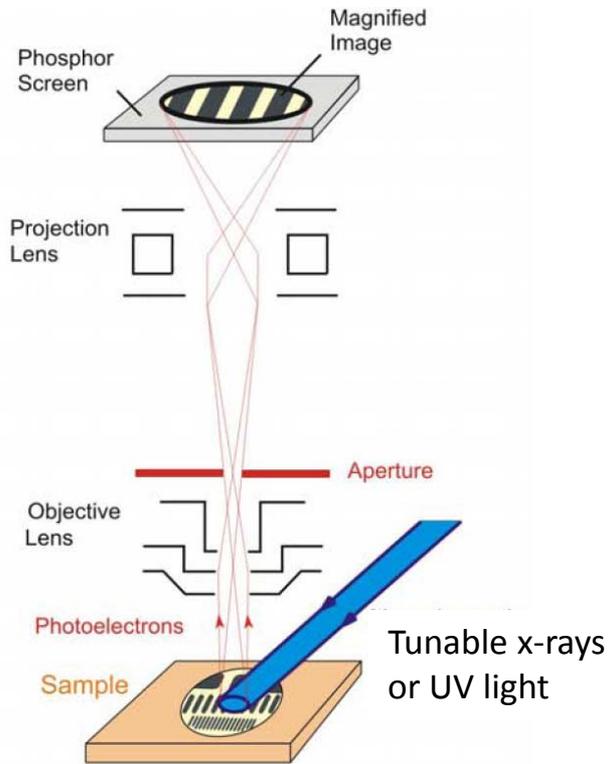
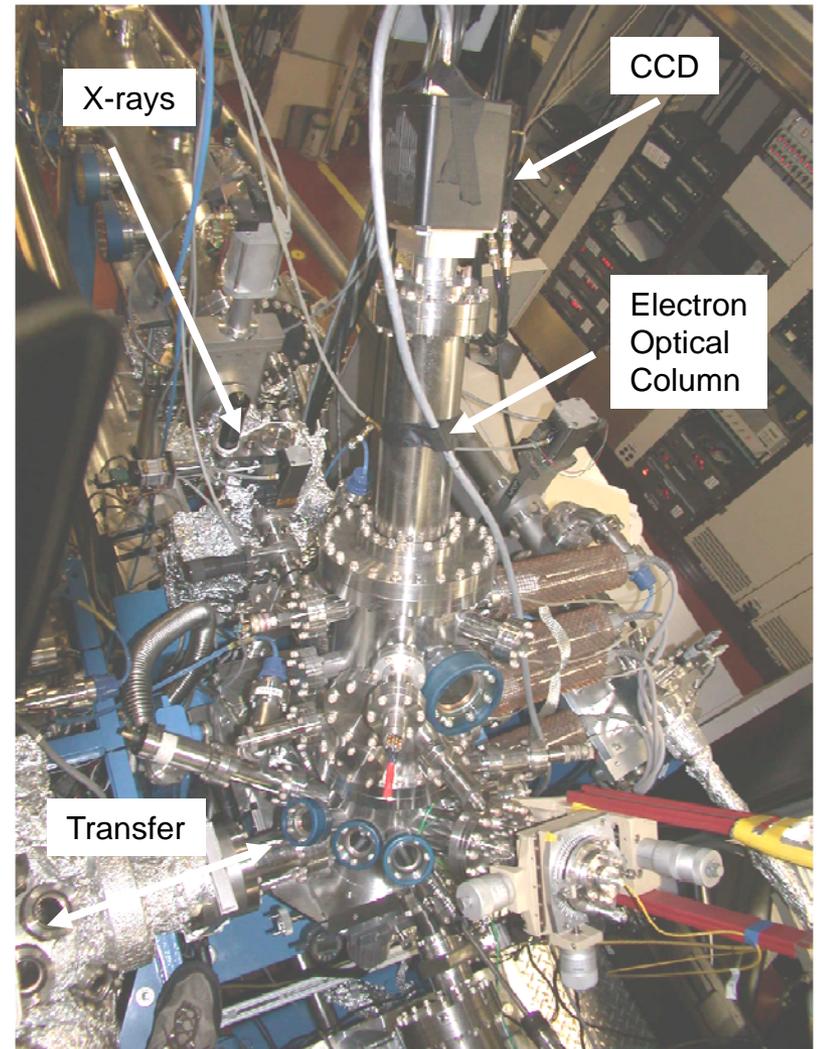


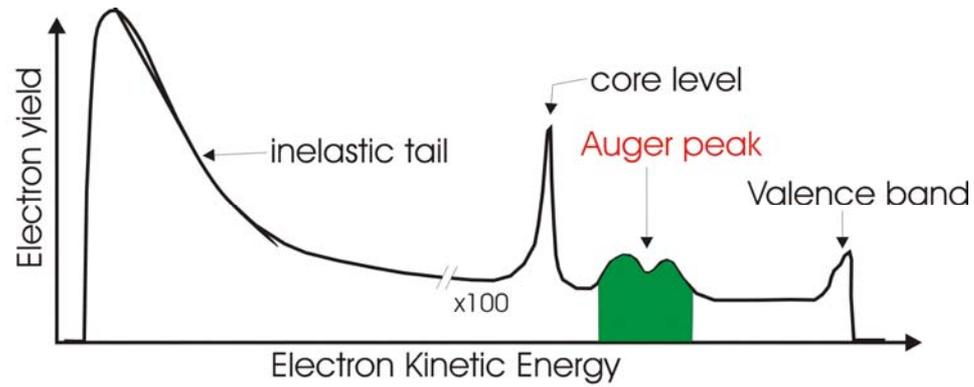
Photo-Emission Electron Microscopy



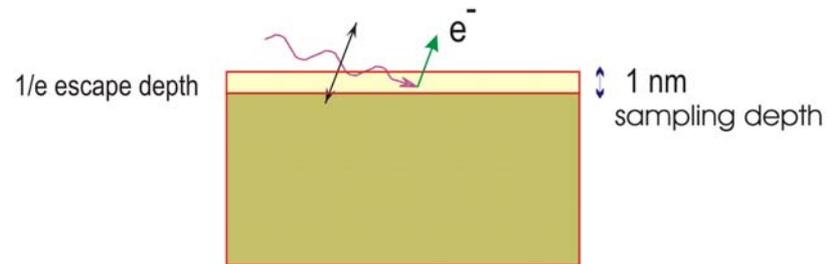
- Full field imaging of electrons (ie. parallel detection)
- Real time
- UV or tunable synchrotron x-rays
- < 5 nm (UV) and 25 nm (x-ray) resolution



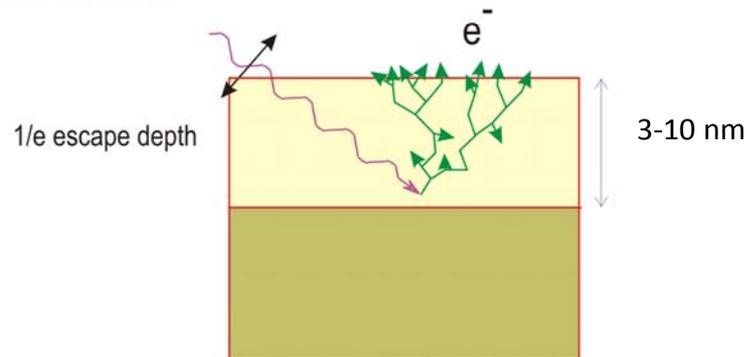
Electron Yield Sampling Depth



Auger Electron Yield



Total Electron Yield



UV Photo-Emission Electron Microscopy



266 nm image of LCLS copper cathode, 30 x 30 microns

-UV imaging

- work function contrast
- < 10 nm resolution

- variable energy

- measure of yield (energy)
- extract local work function

User facilities make things much easier!

- Synchrotrons for x-ray science
- Nanocenters for surface science

Using them is easy, and generally free

Best of all, you get access to materials experts to help you with your experiments